

IGBT

High speed IGBT in Trench and Fieldstop technology
recommended in combination with SiC Diode IDH15S120

IGW40N120H3

1200V high speed switching series third generation

Data sheet

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recommended in combination with SiC Diode IDH15S120

Features:

TRENCHSTOP™ technology offering

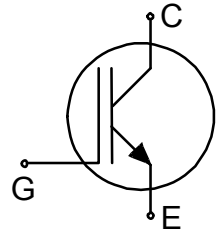
- best in class switching performance: less than 500µJ total switching losses achievable
- very low V_{CEsat}
- low EMI
- maximum junction temperature 175°C
- qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- complete product spectrum and PSpice Models:
<http://www.infineon.com/igbt/>

Applications:

- solar inverters
- uninterruptible power supplies
- welding converters
- converters with high switching frequency

Package pin definition:

- Pin 1 - gate
- Pin 2 & backside - collector
- Pin 3 - emitter



Key Performance and Package Parameters

Type	V_{CE}	I_C	V_{CEsat} , $T_{vj}=25^\circ\text{C}$	T_{vjmax}	Marking	Package
IGW40N120H3	1200V	40A	2.05V	175°C	G40H1203	PG-TO247-3

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Maximum ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	1200	V
DC collector current, limited by T_{vjmax} $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_C	80.0 40.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	160.0	A
Turn off safe operating area $V_{CE} \leq 1200\text{V}$, $T_{vj} \leq 175^\circ\text{C}$	-	160.0	A
Gate-emitter voltage	V_{GE}	± 20	V
Short circuit withstand time $V_{GE} = 15.0\text{V}$, $V_{CC} \leq 600\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ $T_{vj} = 175^\circ\text{C}$	t_{SC}	10	μs
Power dissipation $T_C = 25^\circ\text{C}$ Power dissipation $T_C = 100^\circ\text{C}$	P_{tot}	483.0 220.0	W
Operating junction temperature	T_{vj}	$-40 \dots +175$	$^\circ\text{C}$
Storage temperature	T_{stg}	$-55 \dots +150$	$^\circ\text{C}$
Soldering temperature, wave soldering 1.6 mm (0.063 in.) from case for 10s		260	$^\circ\text{C}$
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction - case	$R_{th(j-c)}$		0.31	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		40	K/W

Electrical Characteristic, at $T_{vj} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{V}$, $I_C = 0.50\text{mA}$	1200	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	$V_{GE} = 15.0\text{V}$, $I_C = 40.0\text{A}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 125^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$	- - -	2.05 2.50 2.70	2.40 - -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 1.00\text{mA}$, $V_{CE} = V_{GE}$	5.0	5.8	6.5	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 1200\text{V}$, $V_{GE} = 0\text{V}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$	- -	- -	250.0 2500.0	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{V}$, $V_{GE} = 20\text{V}$	-	-	600	nA
Transconductance	g_{fs}	$V_{CE} = 20\text{V}$, $I_C = 15.0\text{A}$	-	20.0	-	S

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{ies}	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$	-	2330	-	pF
Output capacitance	C_{oes}		-	150	-	
Reverse transfer capacitance	C_{res}		-	130	-	
Gate charge	Q_G	$V_{CC} = 960V, I_C = 40.0A, V_{GE} = 15V$	-	185.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13.0	-	nH
Short circuit collector current Max. 1000 short circuits Time between short circuits: $\geq 1.0s$	$I_{C(SC)}$	$V_{GE} = 15.0V, V_{CC} \leq 600V, I_{SC} \leq 10\mu s, T_{vj} = 175^{\circ}C$	-	139	-	A

Switching Characteristic, Inductive Load, at $T_{vj} = 25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_{vj} = 25^{\circ}\text{C},$ $V_{CC} = 600\text{V}, I_C = 40.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $r_G = 12.0\Omega, L_{\sigma} = 70\text{nH},$ $C_{\sigma} = 67\text{pF}$ L_{σ}, C_{σ} from Fig. E Energy losses include “tail” and diode (IDH15S120) reverse recovery.	-	30	-	ns
Rise time	t_r		-	57	-	ns
Turn-off delay time	$t_{d(off)}$		-	290	-	ns
Fall time	t_f		-	16	-	ns
Turn-on energy	E_{on}		-	1.93	-	mJ
Turn-off energy	E_{off}		-	1.23	-	mJ
Total switching energy	E_{ts}		-	3.16	-	mJ

Switching Characteristic, Inductive Load, at $T_{vj} = 175^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_{vj} = 175^{\circ}\text{C}$, $V_{CC} = 600\text{V}$, $I_C = 40.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $r_G = 12.0\Omega$, $L_{\sigma} = 70\text{nH}$, $C_{\sigma} = 67\text{pF}$ L_{σ} , C_{σ} from Fig. E Energy losses include “tail” and diode (IDH15S120) reverse recovery.	-	29	-	ns
Rise time	t_r		-	49	-	ns
Turn-off delay time	$t_{d(off)}$		-	366	-	ns
Fall time	t_f		-	48	-	ns
Turn-on energy	E_{on}		-	2.21	-	mJ
Turn-off energy	E_{off}		-	2.66	-	mJ
Total switching energy	E_{ts}		-	4.87	-	mJ

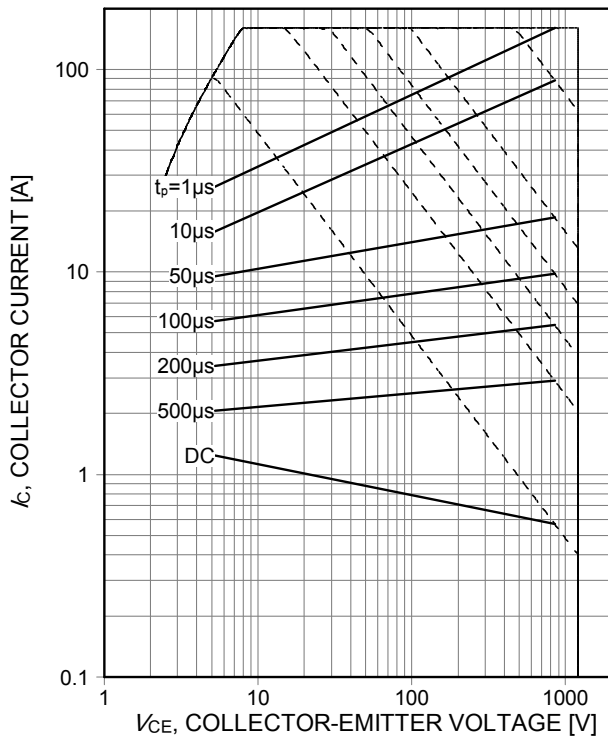


Figure 1. Forward bias safe operating area
($D=0$, $T_C=25^\circ\text{C}$, $T_J\leq 175^\circ\text{C}$; $V_{GE}=15\text{V}$)

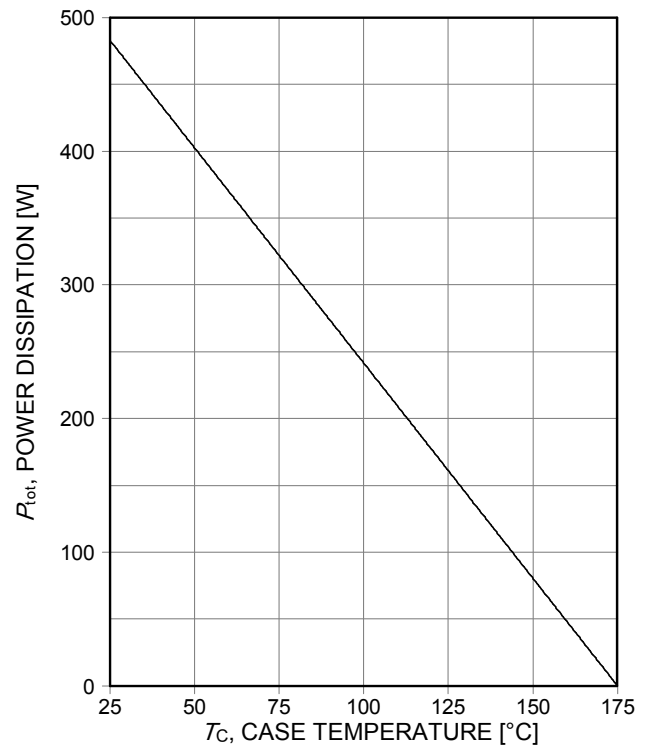


Figure 2. Power dissipation as a function of case temperature
($T_J\leq 175^\circ\text{C}$)

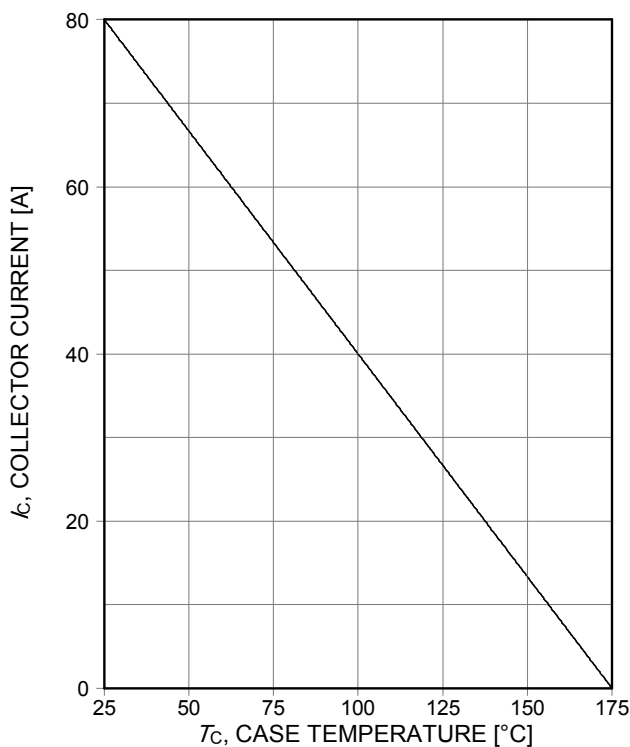


Figure 3. Collector current as a function of case temperature
($V_{GE}\geq 15\text{V}$, $T_J\leq 175^\circ\text{C}$)

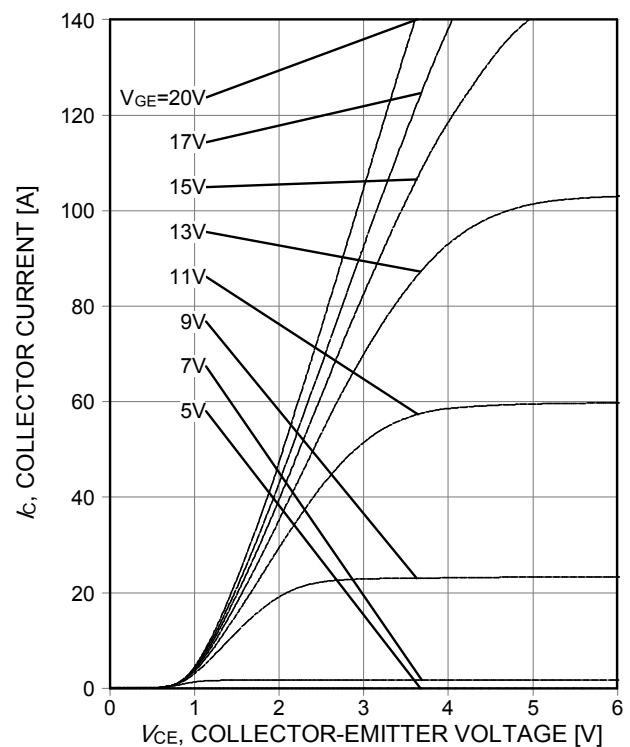


Figure 4. Typical output characteristic
($T_J=25^\circ\text{C}$)

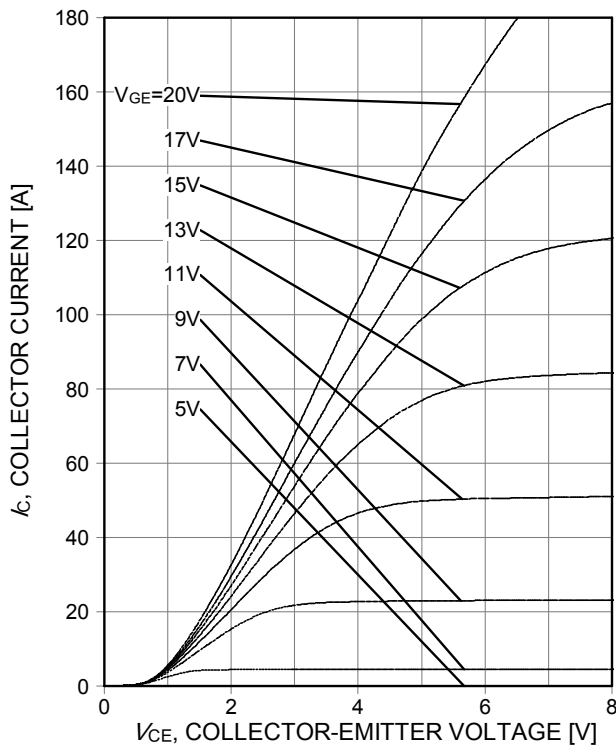


Figure 5. Typical output characteristic
($T_j=175^\circ\text{C}$)

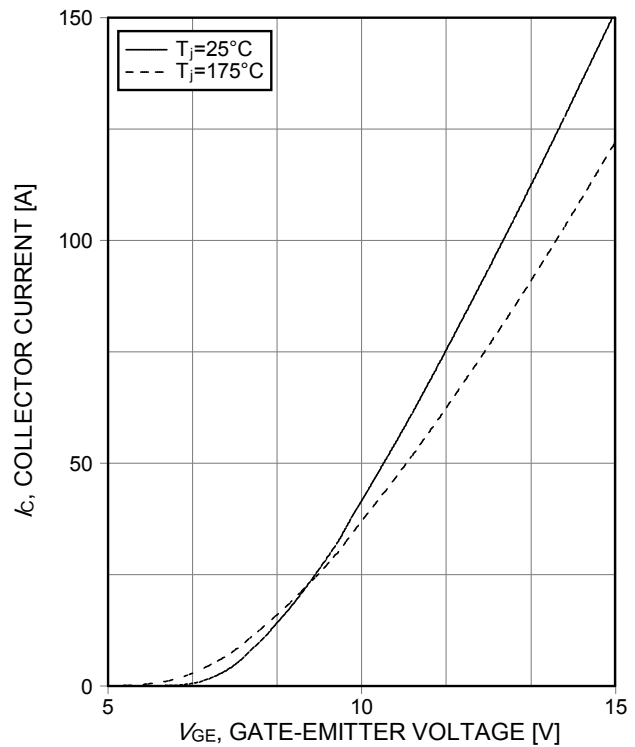


Figure 6. Typical transfer characteristic
($V_{CE}=20\text{V}$)

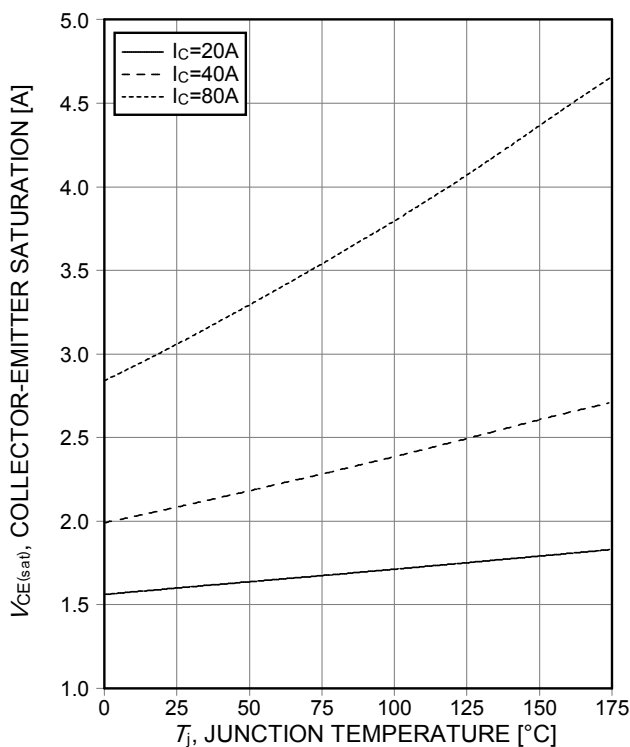


Figure 7. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE}=15\text{V}$)

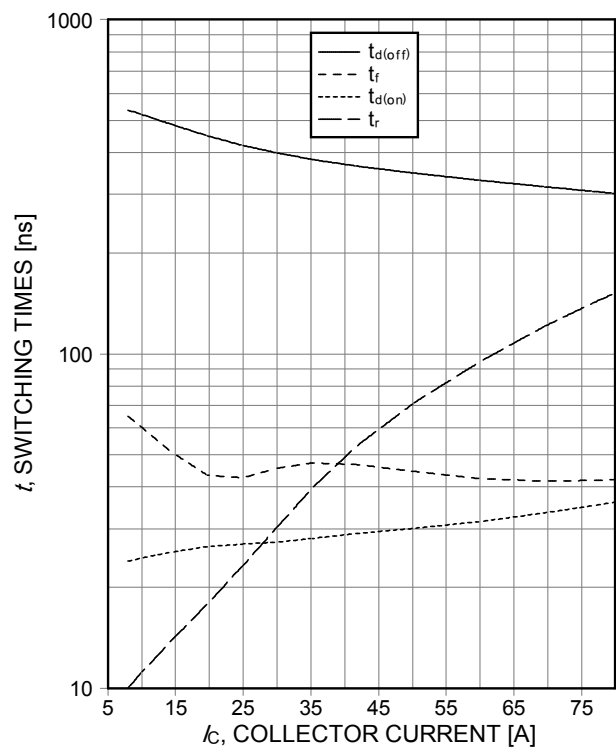


Figure 8. Typical switching times as a function of collector current
(ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=15/0\text{V}$, $R_G=12\Omega$, test circuit in Fig. E)

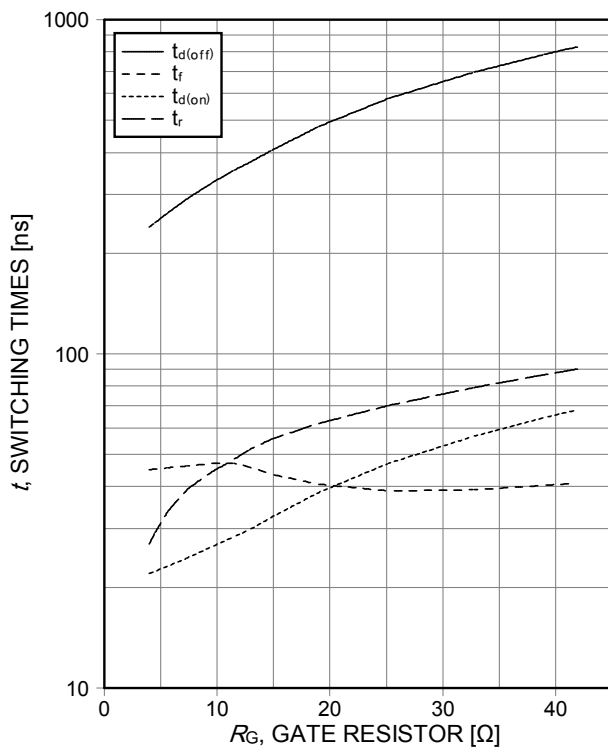


Figure 9. Typical switching times as a function of gate resistor
(ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=40\text{A}$, test circuit in Fig. E)

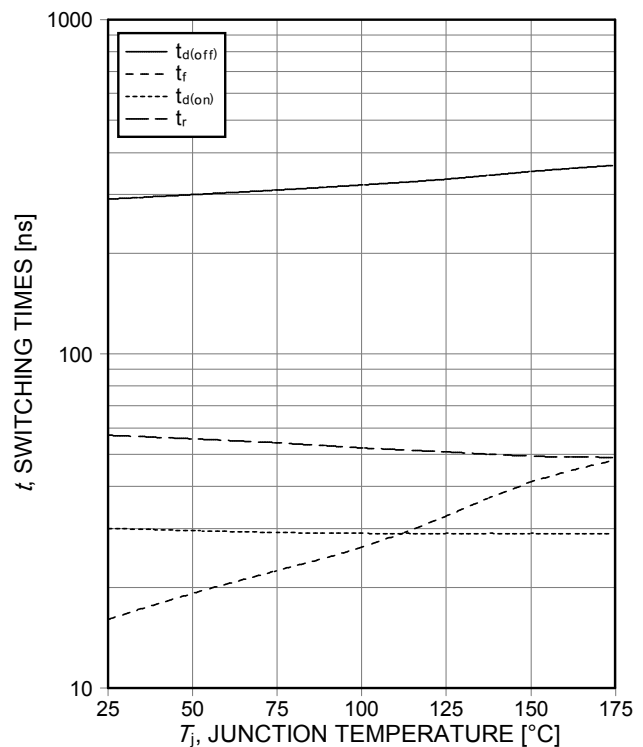


Figure 10. Typical switching times as a function of junction temperature
(ind. load, $V_{CE}=600\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=40\text{A}$, $R_G=12\Omega$, test circuit in Fig. E)

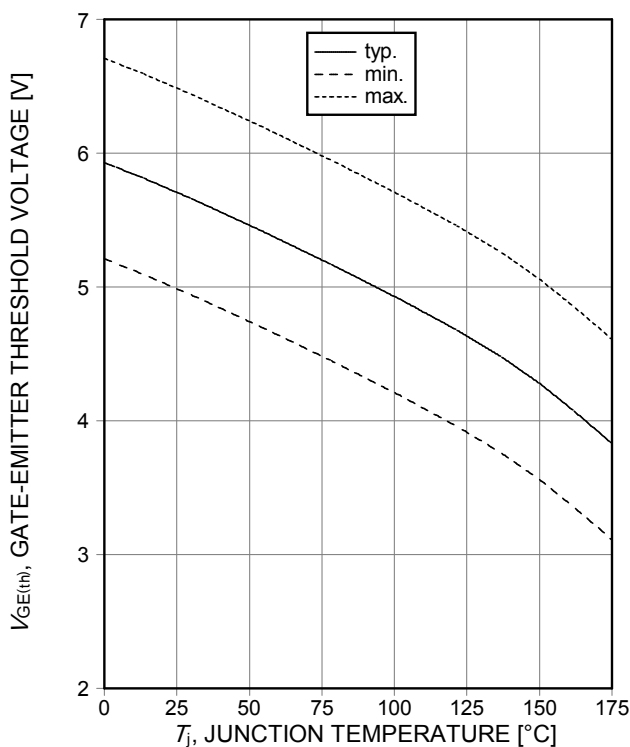


Figure 11. Gate-emitter threshold voltage as a function of junction temperature
($I_C=1\text{mA}$)

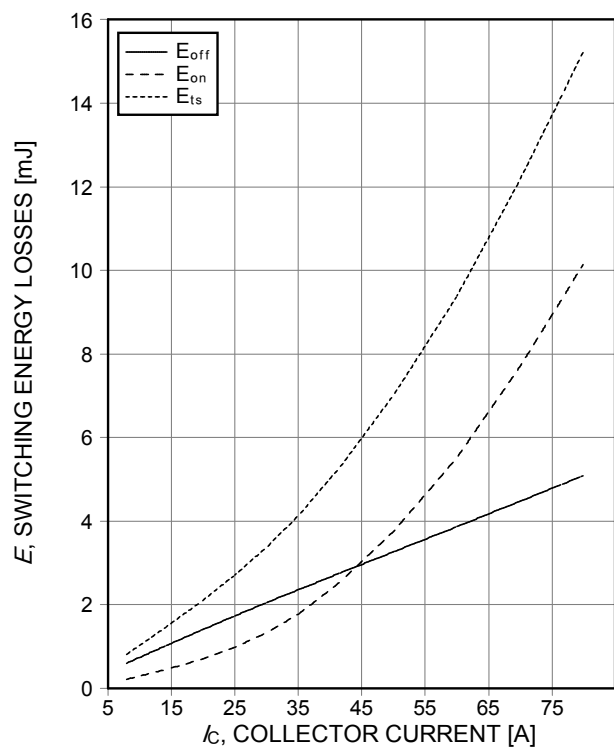


Figure 12. Typical switching energy losses as a function of collector current
(ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=15/0\text{V}$, $R_G=12\Omega$, Diode IDH15S120)

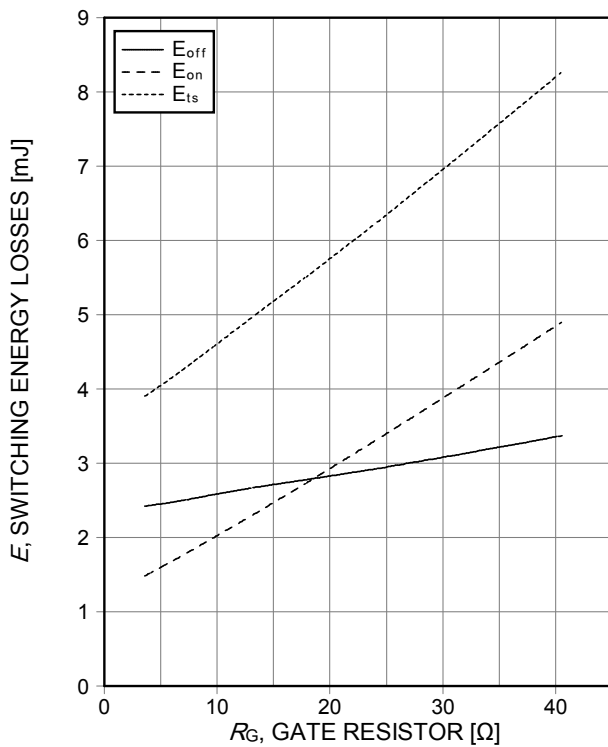


Figure 13. Typical switching energy losses as a function of gate resistor
(ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=40\text{A}$, Diode IDH15S120)

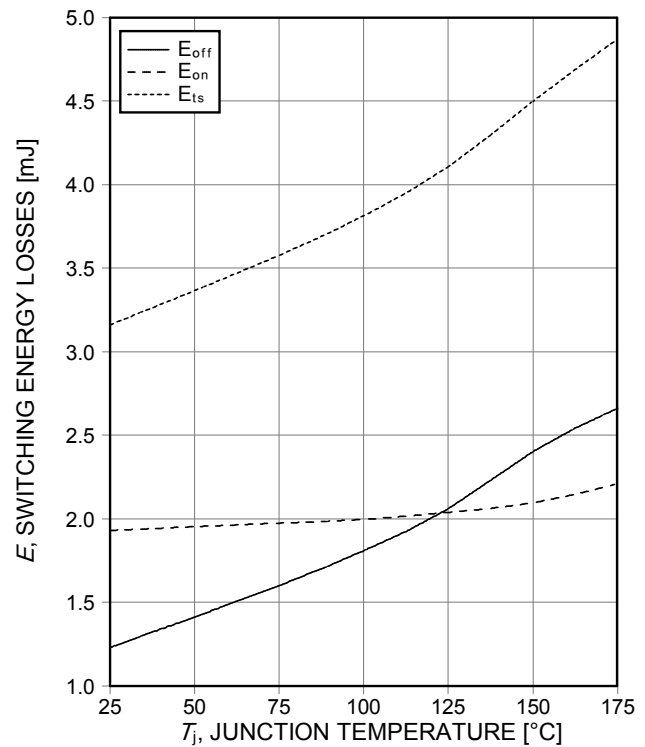


Figure 14. Typical switching energy losses as a function of junction temperature
(ind load, $V_{CE}=600\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=40\text{A}$, $R_G=12\Omega$, Diode IDH15S120)

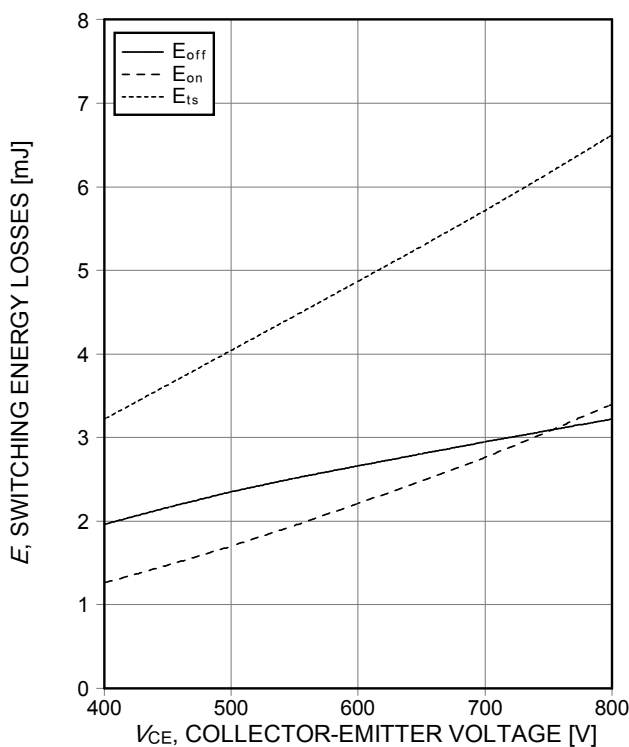


Figure 15. Typical switching energy losses as a function of collector emitter voltage
(ind. load, $T_j=175^\circ\text{C}$, $V_{GE}=15/0\text{V}$, $I_C=40\text{A}$, $R_G=12\Omega$, Diode IDH15S120)

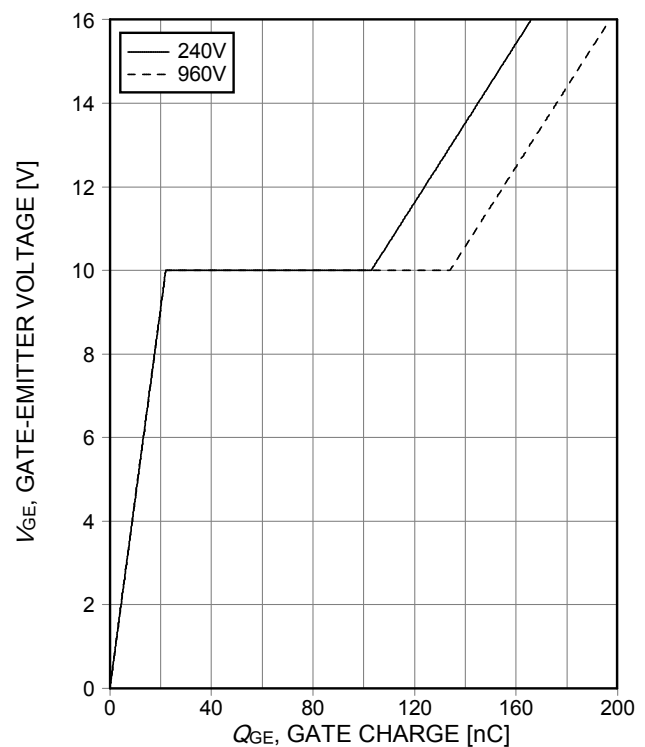


Figure 16. Typical gate charge
($I_C=40\text{A}$)

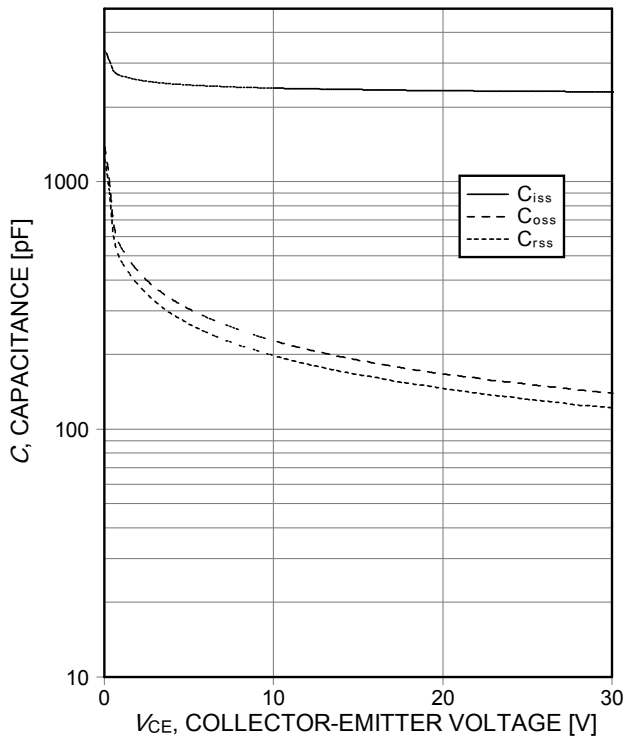


Figure 17. Typical capacitance as a function of collector-emitter voltage
($V_{GE}=0V$, $f=1MHz$)

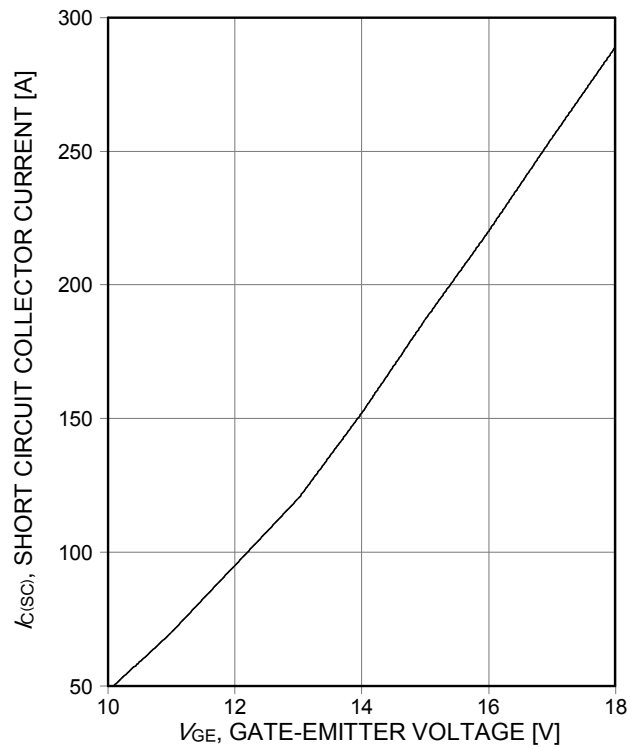


Figure 18. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE} \leq 600V$, start at $T_J=25^\circ C$)

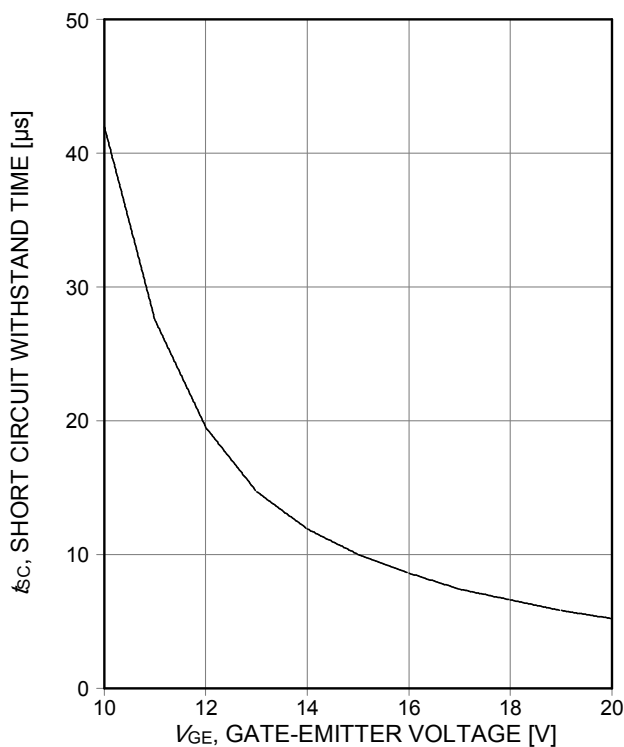


Figure 19. Short circuit withstand time as a function of gate-emitter voltage
($V_{CE} \leq 600V$, start at $T_J \leq 150^\circ C$)

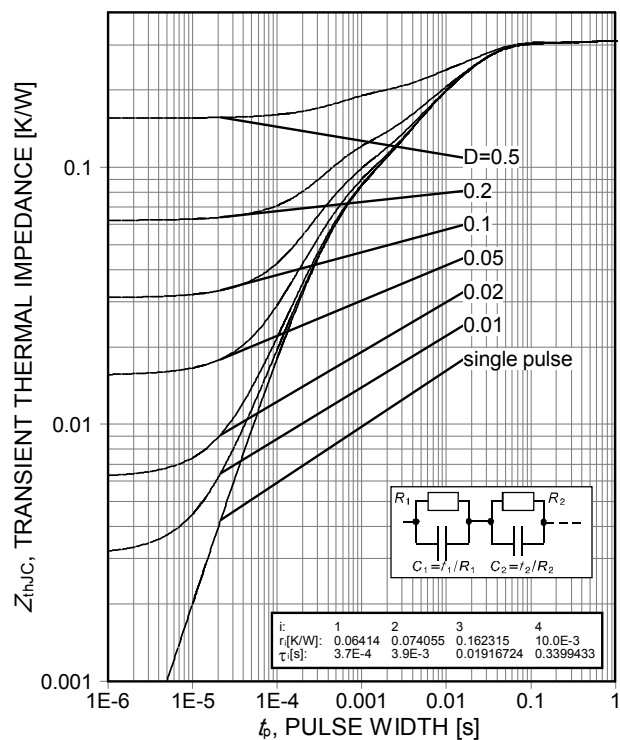
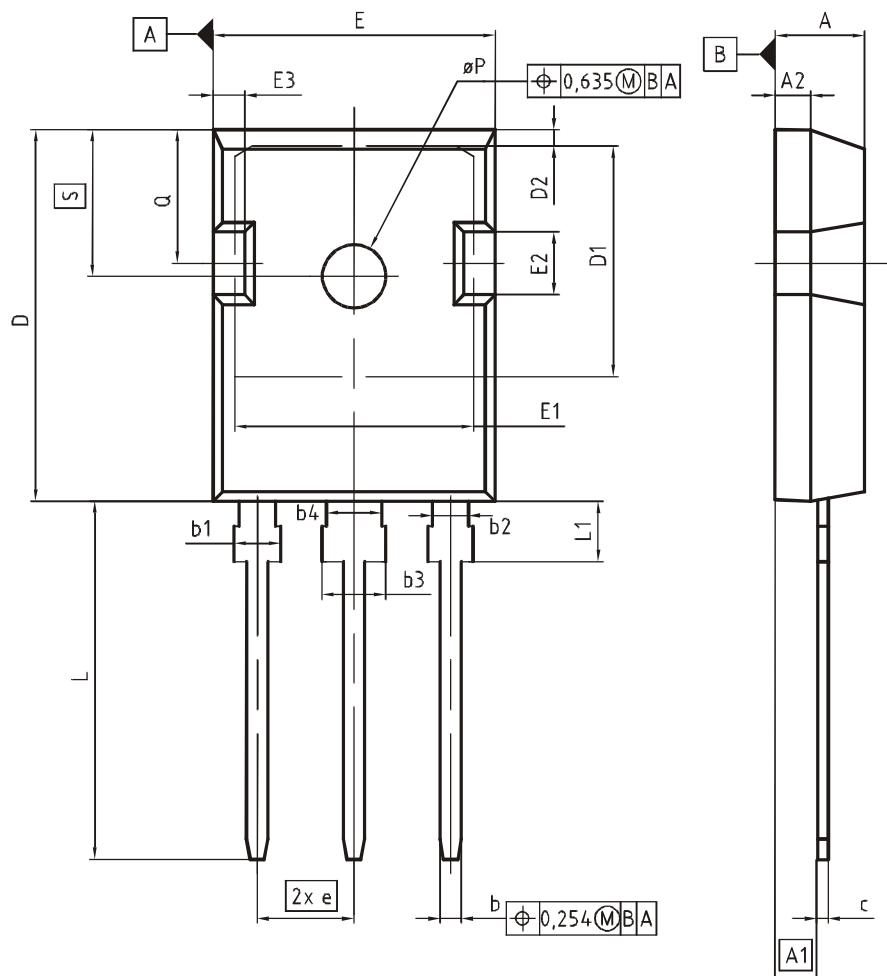
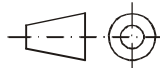


Figure 20. IGBT transient thermal impedance
($D = t_p / T$)

PG-TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

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EUROPEAN PROJECTION 
ISSUE DATE 09-07-2010
REVISION 05

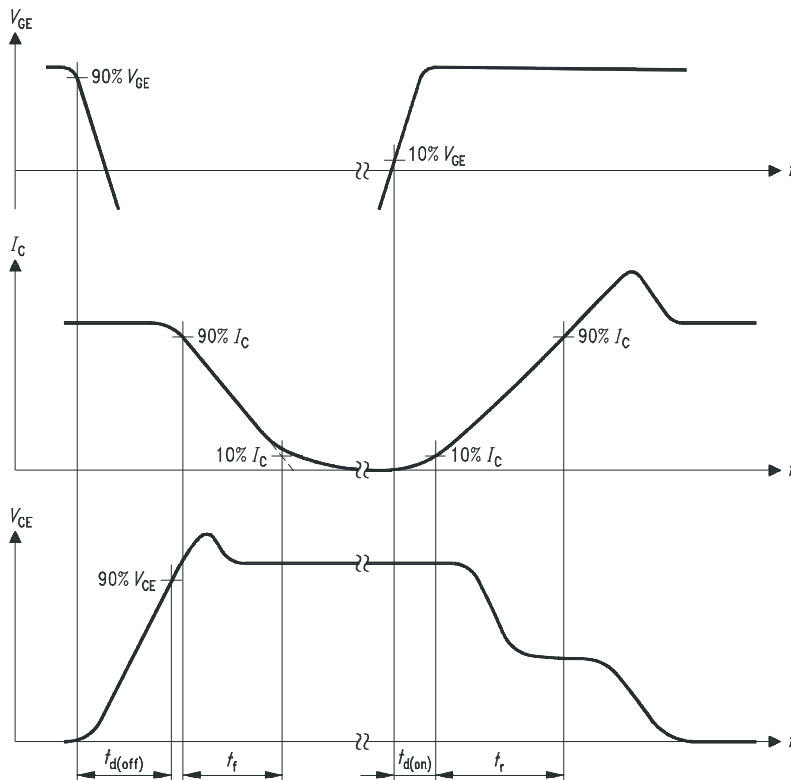


Figure A. Definition of switching times

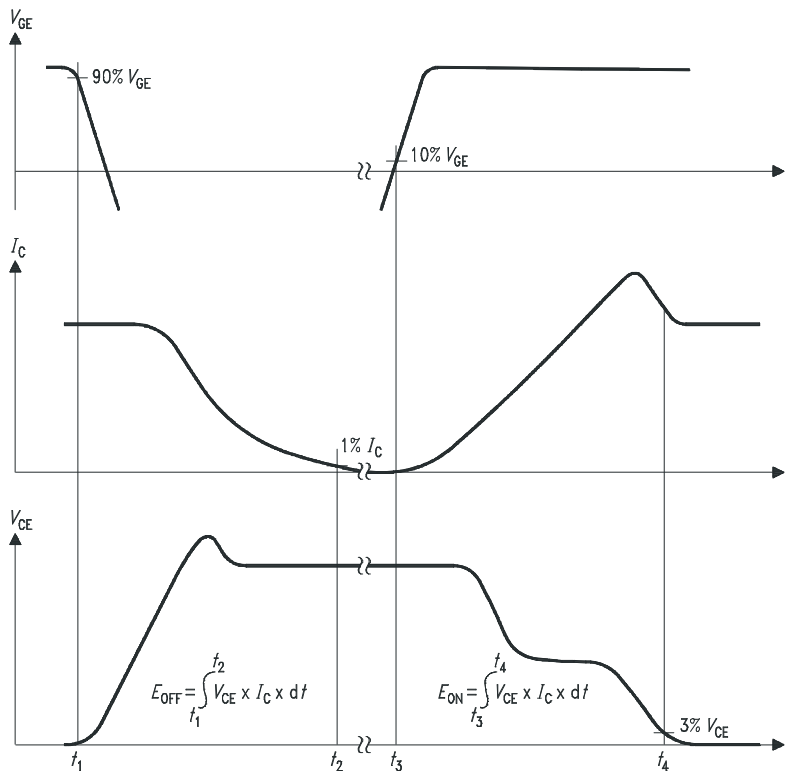


Figure B. Definition of switching losses

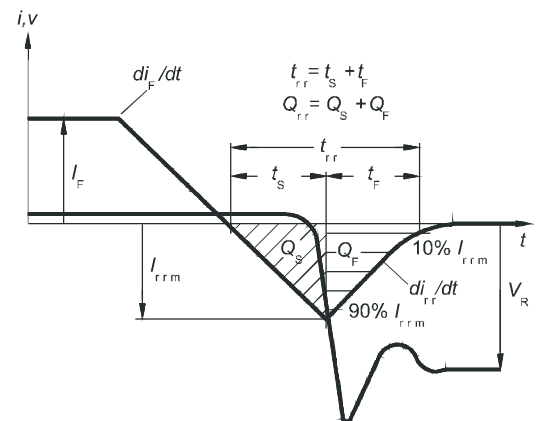


Figure C. Definition of diodes switching characteristics

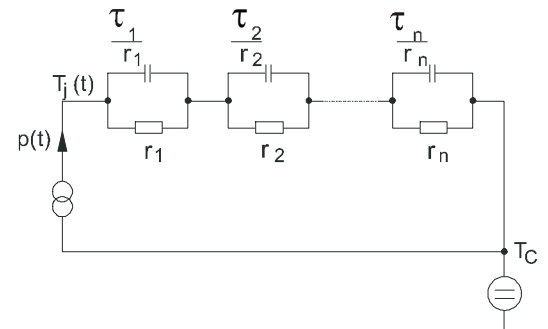


Figure D. Thermal equivalent circuit

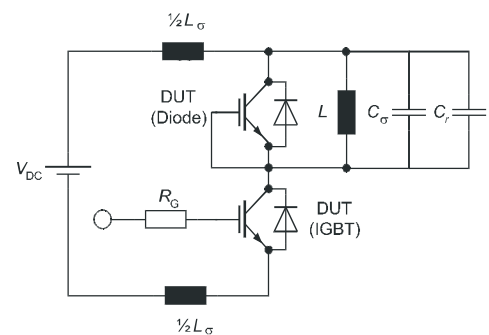


Figure E. Dynamic test circuit

Parasitic inductance L_σ ,
Parasitic capacitor C_σ ,
Relief capacitor C_r
(only for ZVT switching)

Revision History

IGW40N120H3

Revision: 2012-07-31, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2012-07-31	Final data sheet

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Any information within this document that you feel is wrong, unclear or missing at all ?

Your feedback will help us to continuously improve the quality of this document.

Please send your proposal (including a reference to this document) to: erratum@infineon.com

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